

In the Claims:

Please cancel Claims 1-13.

14. (Original) An integrated circuit substrate Read Only Memory (ROM) device, comprising:

- an integrated circuit substrate;
- an insulating layer on the integrated circuit substrate;
- a first conductive layer pattern including a sidewall, on the insulating layer opposite the integrated circuit substrate;
- a thermal oxide layer on the integrated circuit substrate and directly on the sidewall of the first conductive layer pattern;
- a buried doping layer in the integrated circuit substrate beneath the thermal oxide layer; and
- a second conductive layer pattern on at least a portion of the thermal oxide layer and on at least a portion of the first conductive layer pattern.

15. (Original) A ROM device according to Claim 14 wherein the second conductive layer pattern is directly on the first conductive layer pattern opposite the insulating layer.

16. (Original) A ROM device according to Claim 14 wherein the first and second conductive layer patterns both comprise polysilicon.

17. (Original) A ROM device according to Claim 14 further comprising a programming region in the integrated circuit substrate.

18. (Original) A according to Claim 17 wherein the programming region comprises an implant region.

19. (Original) A ROM device according to Claim 14 wherein the second conductive layer pattern is not directly on the sidewall of the first conductive layer pattern.